

Alexander Hardtdegen

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Improved Switching Stability and the Effect of an Internal Series Resistor in $\text{HfO}_2/\text{TiO}_2$ Bilayer ReRAM Cells. IEEE Transactions on Electron Devices, 2018, 65, 3229-3236.	3.0	95
2	Exploiting the switching dynamics of HfO_2 -based ReRAM devices for reliable analog memristive behavior. APL Materials, 2019, 7, .	5.1	94
3	Variability-Aware Modeling of Filamentary Oxide-Based Bipolar Resistive Switching Cells Using SPICE Level Compact Models. IEEE Transactions on Circuits and Systems I: Regular Papers, 2020, 67, 4618-4630.	5.4	72
4	KMC Simulation of the Electroforming, Set and Reset Processes in Redox-Based Resistive Switching Devices. IEEE Nanotechnology Magazine, 2018, 17, 1181-1188.	2.0	21
5	Tuning the Performance of $\text{Pt}/\text{HfO}_2/\text{Ti}/\text{Pt}$ ReRAM Devices Obtained from Plasma-Enhanced Atomic Layer Deposition for HfO_2 Thin Films. ECS Transactions, 2016, 75, 177-184.	0.5	18
6	Internal Cell Resistance as the Origin of Abrupt Reset Behavior in HfO_2 -Based Devices Determined from Current Compliance Series. , 2016, , .		13
7	Evolution of short-range order in chemically and physically grown thin film bilayer structures for electronic applications. Nanoscale, 2020, 12, 13103-13112.	5.6	13
8	Vertical Ge Gate-All-Around Nanowire pMOSFETs With a Diameter Down to 20 nm. IEEE Electron Device Letters, 2020, 41, 533-536.	3.9	13
9	Cation diffusion in polycrystalline thin films of monoclinic HfO_2 deposited by atomic layer deposition. APL Materials, 2020, 8, .	5.1	7